

Silicon PNP Power Transistors

2SA766

DESCRIPTION

- With TO-66 package
- High power dissipation
- Complement to type 2SC1450

APPLICATIONS

- Line-operated vertical deflection output
- Medium power amplifier

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

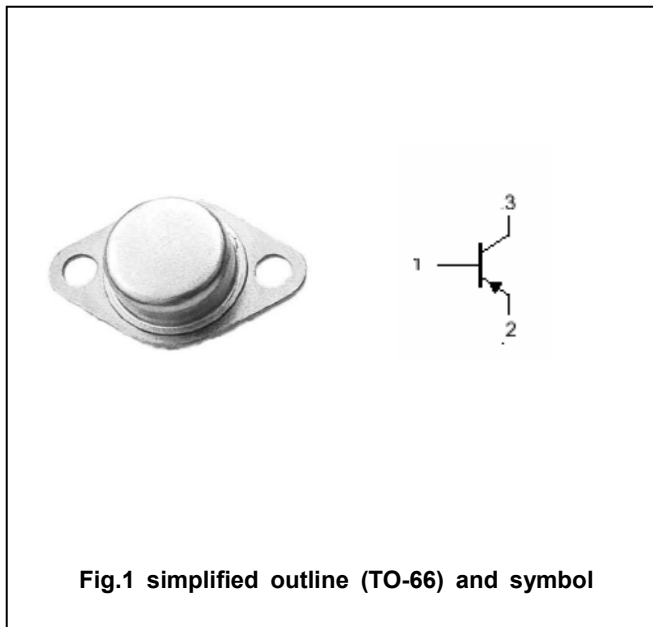


Fig.1 simplified outline (TO-66) and symbol

Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-150	V
V _{CEO}	Collector-emitter voltage	Open base	-150	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-0.4	A
I _{CM}	Collector current-peak		-1.2	A
P _C	Collector power dissipation	T _C ≤80□	20	W
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-65~150	□

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =-0.2A ;L=25mH,R _{BE} =5kΩ	-150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =-1mA ;I _C =0	-5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1A; I _B =-0.1A			-1.0	V
V _{BE-1}	Base-emitter saturation voltage	I _C =-0.1A ; V _{CE} =-5V			-0.8	V
V _{BE-2}	Base-emitter saturation voltage	I _C =-0.5A ; V _{CE} =-5V			-1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =-60V; I _E =0			-30	μA
h _{FE-1}	DC current gain	I _C =-0.1A ; V _{CE} =-5V	35		150	
h _{FE-2}	DC current gain	I _C =-0.5A ; V _{CE} =-5V	35			
f _T	Transition frequency	I _E =0.1A ; V _{CB} =-10V		15		MHz

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PACKAGE OUTLINE



Fig.2 outline dimensions